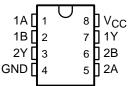
SCES360E - AUGUST 2001 - REVISED JANUARY 2003

- Available in the Texas Instruments
 NanoStar™ and NanoFree™ Packages
- Supports 5-V V_{CC} Operation
- Inputs Accept Voltages to 5.5 V
- Max t_{pd} of 4.7 ns at 3.3 V
- Low Power Consumption, 10-μA Max I_{CC}
- ±24-mA Output Drive at 3.3 V
- Typical V_{OLP} (Output Ground Bounce)
 <0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot)
 >2 V at V_{CC} = 3.3 V, T_A = 25°C
- I_{off} Supports Partial-Power-Down Mode Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
 - 2000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)

DCT OR DCU PACKAGE (TOP VIEW)



YEA OR YZA PACKAGE (BOTTOM VIEW)

			1
GND	04	50	2A
2Y	○3	6 O 7 O	2B
1B	02	70	1Y
1A	O 1	80	Vcc
			,

description/ordering information

This dual 2-input exclusive-OR gate is designed for 1.65-V to 5.5-V V_{CC} operation.

The SN74LVC2G86 performs the Boolean function $Y = A \oplus B$ or $Y = \overline{A}B + A\overline{B}$ in positive logic.

NanoStar™ and NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

A common application is as a true/complement element. If the input is low, the other input is reproduced in true form at the output. If the input is high, the signal on the other input is reproduced inverted at the output.

ORDERING INFORMATION

TA	PACKAGE [†]		ORDERABLE PART NUMBER	TOP-SIDE MARKING [‡]
	NanoStar™ WCSP (DSBGA) – YEA	Reel of 3000	SN74LVC2G86YEAR	СН
-40°C to 85°C	NanoFree™ WCSP (DSBGA) – YZA (Pb-free)	Reel of 3000	SN74LVC2G86YZAR	OH_
10 0 10 00 0	SSOP - DCT	Reel of 3000	SN74LVC2G86DCTR	C86
	VSSOP – DCU	Reel of 3000	SN74LVC2G86DCUR	Coc
	V350P - DC0	Reel of 250	SN74LVC2G86DCUT	C86_

[†] Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

[‡] DCT: The actual top-side marking has three additional characters that designate the year, month, and assembly/test site. DCU: The actual top-side marking has one additional character that designates the assembly/test site. YEA/YZA: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site.



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description/ordering information (continued)

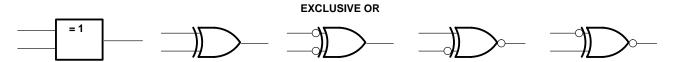
This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

FUNCTION TABLE (each gate)

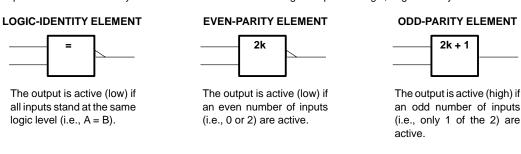
INP	UTS	OUTPUT
Α	В	Υ
L	L	L
L	Н	Н
Н	L	Н
Н	Н	L

exclusive-OR logic

An exclusive-OR gate has many applications, some of which can be represented better by alternative logic symbols.



These are five equivalent exclusive-OR symbols valid for an SN74LVC2G86 gate in positive logic; negation may be shown at any two ports.



SN74LVC2G86 DUAL 2-INPUT EXCLUSIVE-OR GATE

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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage range, V _{CC}	
Input voltage range, V _I (see Note 1)	
Voltage range applied to any output in the high-impedance or pow	ver-off state, V _O
(see Note 1)	
Voltage range applied to any output in the high or low state, VO	
(see Notes 1 and 2)	0.5 V to V _{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$)	
Output clamp current, I _{OK} (V _O < 0)	–50 mA
Continuous output current, IO	±50 mA
Continuous current through V _{CC} or GND	
Package thermal impedance, θ_{JA} (see Note 3): DCT package	220°C/W
	227°C/W
YEA/YZA packag	e 140°C/W
Storage temperature range, T _{stq}	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
 - 2. The value of V_{CC} is provided in the recommended operating conditions table.
 - 3. The package thermal impedance is calculated in accordance with JESD 51-7.



SN74LVC2G86 **DUAL 2-INPUT EXCLUSIVE-OR GATE**

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recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V	Cupply voltage	Operating	1.65	5.5	V
VCC	Supply voltage	Data retention only	1.5		V
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	$0.65 \times V_{CC}$		
\/	High-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7		V
VIH	nigh-level input voltage	$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$	2		v
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	$0.7 \times V_{CC}$		
		V _{CC} = 1.65 V to 1.95 V		$0.35 \times V_{CC}$	
VIL	Low-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	V
VIL.	$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$ $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		0.8	V	
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		$0.3 \times V_{CC}$	1
٧ _I	Input voltage		0	5.5	V
٧o	Output voltage		0	VCC	V
		V _{CC} = 1.65 V		-4	
	High-level output current	V _{CC} = 2.3 V		-8	
loh		VCC = 3 V		-16	mA
		vCC = 3 v		-24	
		V _{CC} = 4.5 V		-32	
		V _{CC} = 1.65 V		4	
		V _{CC} = 2.3 V		8	
I_{OL}	Low-level output current	V _{CC} = 3 V		16	mA
		vCC = 2 v		24	
		V _{CC} = 4.5 V		32	
		V_{CC} = 1.8 V ± 0.15 V, 2.5 V ± 0.2 V		20	
$\Delta t/\Delta v$	Input transition rise or fall rate	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		ns/V	
		$V_{CC} = 5 V \pm 0.5 V$		5	
TA	Operating free-air temperature		-40	85	°C

NOTE 4: All unused inputs of the device must be held at VCC or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	v _{cc}	MIN	TYP† I	MAX	UNIT	
	$I_{OH} = -100 \mu\text{A}$	1.65 V to 5.5 V	V _{CC} -0.1				
	$I_{OH} = -4 \text{ mA}$	1.65 V	1.2				
VOH	$I_{OH} = -8 \text{ mA}$	2.3 V	1.9			V	
	I _{OH} = -16 mA	3 V	2.4			V	
	I _{OH} = -24 mA	3 V	2.3				
	$I_{OH} = -32 \text{ mA}$	4.5 V	3.8				
	$I_{OL} = 100 \mu\text{A}$	1.65 V to 5.5 V			0.1		
	$I_{OL} = 4 \text{ mA}$	1.65 V			0.45	5	
l va.	$I_{OL} = 8 \text{ mA}$	2.3 V			0.3	V	
VOL	$I_{OL} = 16 \text{ mA}$	3 V			0.4	0.4	
	$I_{OL} = 24 \text{ mA}$	3 V			0.55		
	$I_{OL} = 32 \text{ mA}$	4.5 V			0.55		
I _I A or B inputs	$V_I = 5.5 \text{ V or GND}$	0 to 5.5 V			±5	μΑ	
loff	V_I or $V_O = 5.5 V$	0			±10	μΑ	
lcc	$V_I = V_{CC}$ or GND, $I_O = 0$	1.65 V to 5.5 V			10	μΑ	
ΔlCC	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	3 V to 5.5 V			500	μΑ	
C _i	$V_I = V_{CC}$ or GND	3.3 V		5		pF	

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

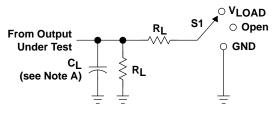
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)		V _{CC} =		V _{CC} =		V _{CC} =		ν _{CC} =		UNIT
	(INPOT)		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A or B	Y	4.1	9.9	2	5.7	1.6	4.7	1.4	3.6	ns

operating characteristics, $T_A = 25^{\circ}C$

Γ	PARAMETER		TEST CONDITIONS		V _{CC} = 1.8 V V _{CC} = 2.5 V		V _{CC} = 3.3 V V _{CC} = 5 V	
L			TEST CONDITIONS	TYP	TYP	TYP	TYP	UNIT
	C _{pd}	Power dissipation capacitance	f = 10 MHz	20	20	20	22	pF

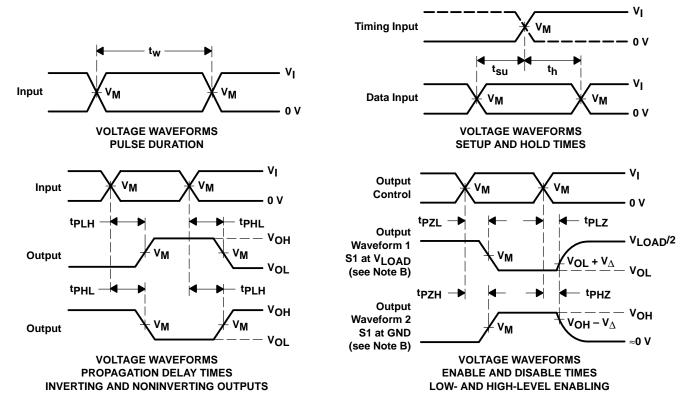
PARAMETER MEASUREMENT INFORMATION



TEST	S1
tPLH/tPHL	Open
tPLZ/tPZL	VLOAD
tPHZ/tPZH	GND

LOAD	CIRCU	JIT
------	-------	-----

.,	INPUTS		.,			_	.,
VCC	٧ı	t _r /t _f	/tf VM VLOAD		CL	RL	$v_{\scriptscriptstyle\Delta}$
1.8 V \pm 0.15 V	VCC	≤2 ns	V _{CC} /2	2×VCC	30 pF	1 k Ω	0.15 V
2.5 V \pm 0.2 V	VCC	≤2 ns	V _{CC} /2	2×V _{CC}	30 pF	500 Ω	0.15 V
3.3 V \pm 0.3 V	3 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
5 V \pm 0.5 V	VCC	≤2.5 ns	V _{CC} /2	2×V _{CC}	50 pF	500 Ω	0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_{O} = 50 \Omega$.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tplH and tpHL are the same as tpd.
- H. All parameters and waveforms are not applicable to all devices.

Figure 1. Load Circuit and Voltage Waveforms



DCT (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE

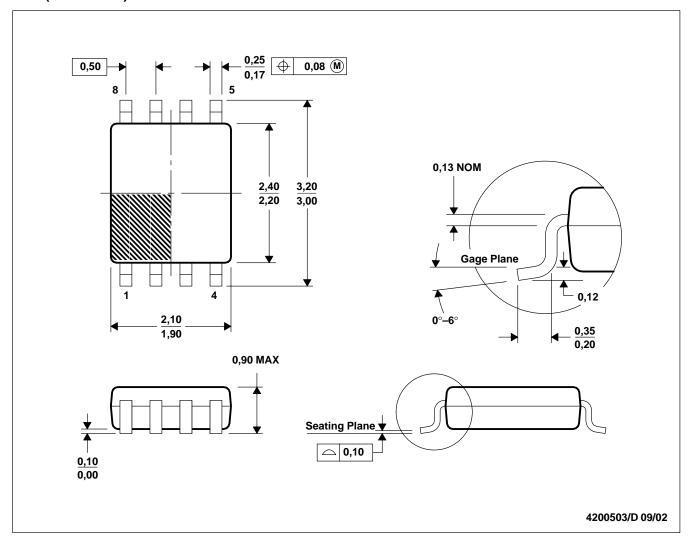


NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion
- D. Falls within JEDEC MO-187 variation DA.

DCU (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE

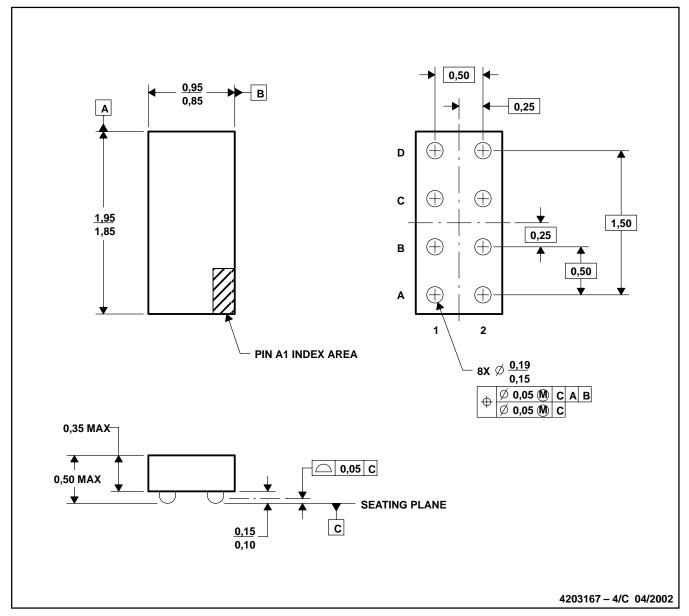


NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. Falls within JEDEC MO-187

YEA (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY

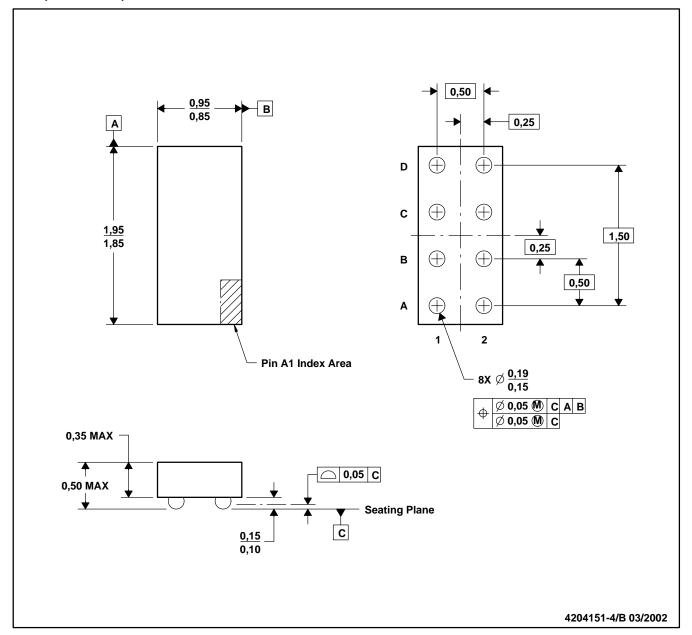


NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. NanoStar package configuration.
- D. Package complies to JEDEC MO-211 variation EB.
- E. This package is tin-lead (SnPb). Refer to the 8 YZA package (drawing 4204151) for lead-free.

YZA (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY



- NOTES: A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. NanoFree™ package configuration.
 - D. Package complies to JEDEC MO-211 variation EB.
 - E. This package is lead-free. Refer to the 8 YEA package (drawing 4203167) for tin-lead (SnPb).

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